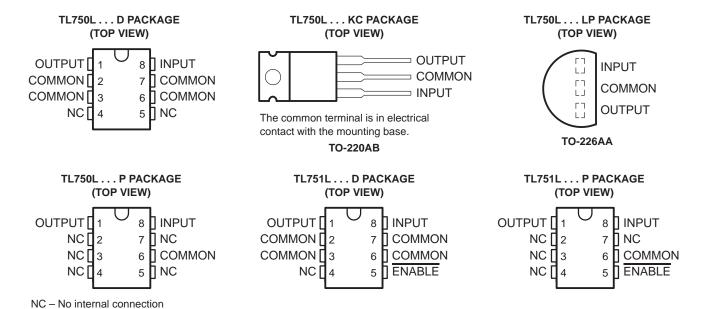
- Very Low Dropout Voltage, Less Than 0.6 V at 150 mA
- Very Low Quiescent Current
- TTL- and CMOS-Compatible Enable on TL751L Series
- 60-V Load-Dump Protection

- Reverse Transient Protection Down to –50 V
- Internal Thermal-Overload Protection
- Overvoltage Protection
- Internal Overcurrent-Limiting Circuitry
- Less Than 500-μA Disable (TL751L Series)



DEVICE COMPONENT COUNT		
Transistors	20	
JFETs	2	
Diodes	5	
Resistors	16	

description

The TL750L and TL751L series are low-dropout positive-voltage regulators specifically designed for battery-powered systems. These devices incorporate overvoltage and current-limiting protection circuitry, along with internal reverse-battery protection circuitry to protect the devices and the regulated system. The series is fully protected against 60-V load-dump and reverse-battery conditions. Extremely low quiescent current during full-load conditions makes these devices ideal for standby power systems.

The TL750L and TL751L series of fixed-output voltage regulators offers 5-V, 8-V, 10-V, and 12-V options. The TL751L series has the addition of an enable (ENABLE) input. When ENABLE is high, the regulator output is placed in the high-impedance state. This gives the designer complete control over power up, power down, or emergency shutdown.



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description (continued)

The TL750LxxC and the TL751LxxC series are characterized for operation over the virtual junction temperature range of 0°C to 125°C. The TL750L05Q and TL751L05Q are characterized for operation over the virtual junction temperature range of –40°C to 125°C.

AVAILABLE OPTIONS

	V _O TYP		PA	CKAGED DEVICE	S	
TJ	AT 25°C	SMALL HEAT-SII OUTLINE MOUNTI (D) (KC)		PLASTIC CYLINDRICAL (LP)	PLASTIC DIP (P)	CHIP FORM (Y)
	5 V	TL750L05CD TL751L05CD	TL750L05CKC	TL750L05CLP	TL750L05CP TL751L05CP	TL750L05Y
0°C to 125°C	8 V	TL750L08CD TL751L08CD	TL750L08CKC	TL750L08CLP	TL750L08CP TL751L08CP	TL750L08Y
0 0 10 125 0	10 V	TL750L10CD TL751L10CD	TL750L10CKC	TL750L10CLP	TL750L10CP TL751L10CP	TL750L10Y
	12 V	TL750L12CD TL751L12CD	TL750L12CKC	TL750L12CLP	TL750L12CP TL751L12CP	TL750L12Y
-40°C to 125°C	5 V	TL750L05QD TL751L05QD	-	_	-	_

The D, KTE, and LP packages are available taped and reeled. The KTP is only available taped and reeled. Add R suffix to device type (e.g., TL750L05CDR). Chip forms are tested at 25°C.

absolute maximum ratings over operating junction temperature range (unless otherwise noted)

		TL750Lxx TL751Lxx	UNIT
Continuous input voltage			V
Transient input voltage, T _A = 25°C (see Note 1)			V
Continuous reverse input voltage			V
Transient reverse input voltage: t ≤ 100 ms	-50	V	
	D package	97	°C
Package thermal impedance, θ_{JA} (see Notes 2 and 3)	KC package	22	
Package merman impedance, σχή (see Notes 2 and 3)	LP package	156	
	P package	127	
Virtual junction temperature range, T _J		-40 to 150	°C
Lead temperature 1,6 mm (1/16 inch) for 10 seconds		260	°C
Storage temperature range, T _{Stg}	•	-65 to 150	°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The transient input voltage rating applies to the waveform shown in Figure 1.

- 2. Maximum power dissipation is a function of $T_J(max)$, θ_{JA} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can impact reliability.
- 3. The package thermal impedance is calculated in accordance with JESD 51, except for through-hole packages, which use a trace length of zero.



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recommended operating conditions over recommended operating junction temperature range (unless otherwise noted)

			MIN	MAX	UNITS
			6	26	
Innut voltage V			9	26	V
Input voltage, V _I		TL75xL10	11	26	V
		TL75xL12	13	26	
High-level ENABLE input voltage, VIH			2	15	V
Low local FNARIE Constructions V. T.	T _A = 25°C	TL751Lxx	-0.3	0.8	V
Low-level ENABLE input voltage, V _{IL} †	T _A = full range‡	TL751Lxx	-0.15	0.8	V
Output current range, IO		TL75xLxx	0	150	mA
On a setting wint valid to a term a set was T		TL75xLxxC	0	125	°C
Operating virtual junction temperature, TJ		TL75xL05Q	-40	125	-0

[†] The algebraic convention, in which the least positive (most negative) value is designated minimum, is used in this data sheet for ENABLE voltage levels and temperature only.

electrical characteristics, V_I = 14 V, I_O = 10 mA, T_J = 25°C (unless otherwise noted) (see Note 4)

PARAMETER TEST CONDITIONS§		TL750L05 TEST CONDITIONS TL751L05					UNIT
		MIN	TYP	MAX			
Output voltage		4.80	5	5.2	V		
Output voltage	$T_J = T_J(min)$ to 125°C¶	4.75		5.25	V		
Input regulation voltage	V _I = 9 V to 16 V		5	10	mV		
input regulation voltage	V _I = 6 V to 26 V		6	30	IIIV		
Ripple rejection	$V_1 = 8 \text{ V to } 18 \text{ V}, \qquad f = 120 \text{ Hz}$	60	65		dB		
Output regulation voltage	I _O = 5 mA to 150 mA		20	50	mV		
Dropout voltage	$I_O = 10 \text{ mA}$			0.2	V		
Dropout voltage	I _O = 150 mA			0.6	V		
Output noise voltage	f = 10 Hz to 100 kHz		500		μV		
	$I_{O} = 150 \text{ mA}$		10	12			
Input bias current	$V_I = 6 \text{ V to } 26 \text{ V}, \qquad I_O = 10 \text{ mA}, \qquad T_J = T_J(\text{min}) \text{ to } 125^{\circ}\text{C}$		1	2	mA		
	ENABLE > 2 V			0.5			

 $[\]S$ Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1- μ F capacitor across the input and a 10- μ F capacitor, with equivalent series resistance of less than 0.4 Ω , across the output.

NOTE 4: For TL750L05Q/TL751L05Q, all characteristics are measured with a 0.1-μF tantalum capacitor on the output with equivalent series resistance within the guidelines shown in Figure 4.



[‡] Full range is 0°C to 125°C for the TL75xLxxC devices, and -40°C to 125°C for the TL75L05Q devices.

[¶]T_I(min) is 0°C for the TL75xLxxC devices, and -40°C for the TL75xLxxQ devices.

TL750L, TL751L SERIES LOW-DROPOUT VOLTAGE REGULATORS

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electrical characteristics, $V_I = 14 \text{ V}$, $I_O = 10 \text{ mA}$, $T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER TEST CONDITIONS [†]		TL750L08 TEST CONDITIONS† TL751L08				
		MIN	TYP	MAX		
Output voltage		7.68	8	8.32	V	
Output voltage	$T_J = 0$ °C to 125°C	7.6		8.4	V	
Input regulation voltage	V _I = 10 V to 17 V		10	20	mV	
Input regulation voltage	V _I = 9 V to 26 V		25	50	IIIV	
Ripple rejection	V _I = 11 V to 21 V, f = 120 Hz	60	65		dB	
Output regulation voltage	$I_O = 5$ mA to 150 mA		40	80	mV	
Dropout voltage	$I_O = 10 \text{ mA}$			0.2	V	
Dropout voltage	I _O = 150 mA			0.6	V	
Output noise voltage	f = 10 Hz to 100 kHz		500		μV	
	I _O = 150 mA		10	12		
Input bias current	$V_{I} = 9 \text{ V to } 26 \text{ V},$ $I_{O} = 10 \text{ mA},$ $T_{J} = 0^{\circ}\text{C to } 125^{\circ}\text{C}$		1	2	mA	
	ENABLE > 2 V			0.5		

 $[\]overline{1}$ Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1-μF capacitor across the input and a 10-μF capacitor, with equivalent series resistance of less than 0.4 Ω , across the output.

electrical characteristics, $V_I = 14 \text{ V}$, $I_O = 10 \text{ mA}$, $T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS [†]		TL750L10 TL751L10			
		MIN	TYP	MAX		
Output voltage		9.6	10	10.4	V	
Output voltage	$T_J = 0$ °C to 125°C	9.5		10.5	V	
Input regulation voltage	V _I = 12 V to 19 V		10	25	mV	
Input regulation voltage	V _I = 11 V to 26 V		30	60	IIIV	
Ripple rejection	$V_{I} = 12 \text{ V to } 22 \text{ V}, \qquad f = 120 \text{ Hz}$	60	65		dB	
Output regulation voltage	$I_O = 5 \text{ mA to } 150 \text{ mA}$		50	100	mV	
Dropout voltage	$I_O = 10 \text{ mA}$			0.2	V	
Dropout voltage	I _O = 150 mA			0.6	V	
Output noise voltage	f = 10 Hz to 100 kHz		700		μV	
	I _O = 150 mA		10	12		
Input bias current	$V_{I} = 11 \text{ V to } 26 \text{ V}, \qquad I_{O} = 10 \text{ mA}, \qquad T_{J} = 0^{\circ}\text{C to } 125^{\circ}\text{C}$		1	2	mA	
	ENABLE > 2 V			0.5		

[†] Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1- μ F capacitor across the input and a 10- μ F capacitor, with equivalent series resistance of less than 0.4 Ω , across the output.

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electrical characteristics, V_I = 14 V, I_O = 10 mA, T_J = 25°C (unless otherwise noted)

PARAMETER	TEST CONDITIONS†	TL750L12 TL751L12			UNIT	
		MIN	TYP	MAX		
Output voltage		11.52	12	12.48	V	
Output voltage	$T_J = 0$ °C to 125°C	11.4		12.6	V	
Input regulation voltage	V _I = 14 V to 19 V		15	30	mV	
	V _I = 13 V to 26 V		20	40	IIIV	
Ripple rejection	V _I = 13 V to 23 V, f = 120 Hz	50	55		dB	
Output regulation voltage	I _O = 5 mA to 150 mA		50	120	mV	
Dropout voltogo	I _O = 10 mA			0.2	V	
Dropout voltage	I _O = 150 mA			0.6	V	
Output noise voltage	f = 10 Hz to 100 kHz		700		μV	
Input bias current	I _O = 150 mA		10	12		
	$V_I = 13 \text{ V to } 26 \text{ V}, I_O = 10 \text{ mA}, T_J = 0^{\circ}\text{C to } 125^{\circ}\text{C}$		1	2	mA	
	ENABLE > 2 V			0.5		

[†] Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1- μ F capacitor across the input and a 10- μ F capacitor, with equivalent series resistance of less than 0.4 Ω , across the output.

electrical characteristics, $V_I = 14 \text{ V}$, $I_O = 10 \text{ mA}$, $T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	TTOT GOVERNO	TL	TL750L05Y			
PARAMETER	TEST CONDITIONS†	MIN	TYP	MAX	UNIT	
Output voltage			5		V	
Input regulation voltage	V _I = 9 V to 16 V		5		mV	
	V _I = 6 V to 26 V		6		IIIV	
Ripple rejection	$V_I = 8 \text{ V to } 18 \text{ V}, f = 120 \text{ Hz}$		65		dB	
Output regulation voltage	I _O = 5 mA to 150 mA		20		mV	
Output noise voltage	f = 10 Hz to 100 kHz		500		μV	
Input bias current	I _O = 150 mA		10		mΛ	
	$V_I = 6 \text{ V to } 26 \text{ V}, I_O = 10 \text{ mA}$	1			mA	

[†] Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1- μ F capacitor across the input and a 10- μ F capacitor, with equivalent series resistance of less than 0.4 Ω , across the output.

TL750L, TL751L SERIES LOW-DROPOUT VOLTAGE REGULATORS

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electrical characteristics, V_I = 14 V, I_O = 10 mA, T_J = 25°C (unless otherwise noted)

PARAMETER	TEST SOMBITIONS!	TL750L08	UNIT	
FARAINETER	TEST CONDITIONS†	MIN TYP	MAX	UNIT
Output voltage		8		V
Input regulation voltage	V _I = 10 V to 17 V	10		mV
	V _I = 9 V to 26 V	25		IIIV
Ripple rejection	$V_{I} = 11 \text{ V to } 21 \text{ V}, \qquad f = 120 \text{ Hz}$	65		dB
Output regulation voltage	I _O = 5 mA to 150 mA	40		mV
Output noise voltage	f = 10 Hz to 100 kHz	500		μV
Input hige current	I _O = 150 mA	10		mA
Input bias current	$V_I = 9 \text{ V to } 26 \text{ V}, \qquad I_O = 10 \text{ mA}$	1		IIIA

[†] Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1- μ F capacitor across the input and a 10- μ F capacitor, with equivalent series resistance of less than 0.4 Ω , across the output.

electrical characteristics, $V_I = 14 \text{ V}$, $I_O = 10 \text{ mA}$, $T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	TTOT GOVERNOUS!	TL750L10Y	UNIT
PARAMETER	TEST CONDITIONS [†]	MIN TYP MAX	UNII
Output voltage		10	V
Input regulation voltage	V _I = 12 V to 19 V	10	mV
	V _I = 11 V to 26 V	30	IIIV
Ripple rejection	$V_I = 12 \text{ V to } 22 \text{ V}, \qquad f = 120 \text{ Hz}$	65	dB
Output regulation voltage	I _O = 5 mA to 150 mA	50	mV
Output noise voltage	f = 10 Hz to 100 kHz	700	μV
Input bias current	I _O = 150 mA	10	
	$V_I = 11 \text{ V to 26 V}, \qquad I_O = 10 \text{ mA}$	1	mA

[†] Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1- μ F capacitor across the input and a 10- μ F capacitor, with equivalent series resistance of less than 0.4 Ω , across the output.

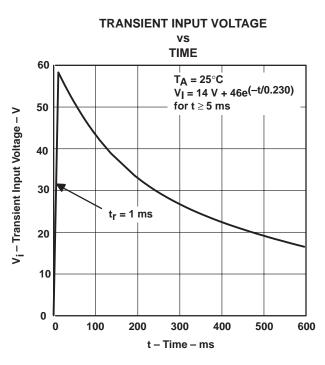
electrical characteristics, V_I = 14 V, I_O = 10 mA, T_J = 25°C (unless otherwise noted)

PARAMETER	TEST SOMBITIONS!	TL750L12Y	UNIT
FARAINETER	TEST CONDITIONS†	MIN TYP MAX	UNIT
Output voltage		12	V
Input regulation voltage	V _I = 14 V to 19 V	15	mV
Input regulation voltage	V _I = 13 V to 26 V	20	IIIV
Ripple rejection	V _I = 13 V to 23 V, f = 120 Hz	55	dB
Output regulation voltage	I _O = 5 mA to 150 mA	50	mV
Output noise voltage	f = 10 Hz to 100 kHz	700	μV
Input biog current	I _O = 150 mA	10	mA
Input bias current	$V_I = 13 \text{ V to 26 V}, \qquad I_O = 10 \text{ mA}$	1	IIIA

[†] Pulse-testing techniques are used to maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.1- μ F capacitor across the input and a 10- μ F capacitor, with equivalent series resistance of less than $0.4~\Omega$, across the output.



TYPICAL CHARACTERISTICS



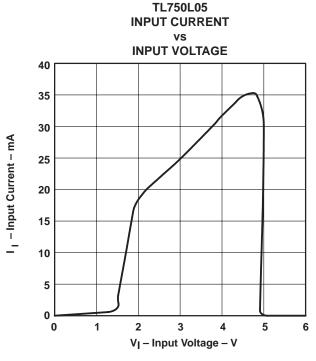
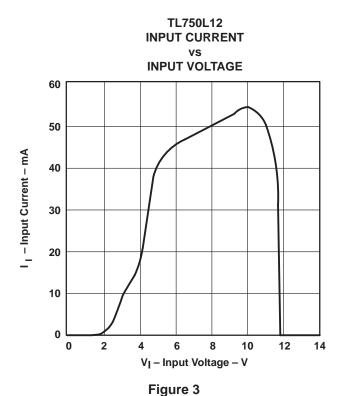


Figure 1

Figure 2





TYPICAL CHARACTERISTICS

TL750L05 EQUIVALENT SERIES RESISTANCE vs

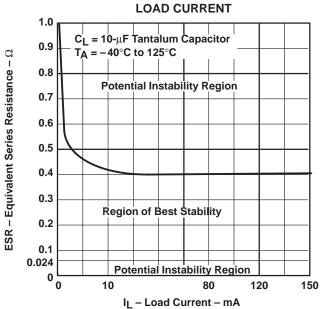


Figure 4

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